

SB7560S 75A SCRs

FEATURES

- High thermal cycling performance
- High voltage capacity
- Very high current surge capability

APPLICATIONS

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control







Parameters Summary					
VD/VR:1200/1600V	IT(RMS)	:75A IGT :60n	nA		
A(2) G(3)	⊸K(1)	1 ₂₃ TO-247	1 2 3 TO-3F Insular		

ABSOLUTE MAXIMUM RATINGS						
Parameter	Symbol	Value	Unit			
Storage junction temperature range	Tstg	- 40 ∼150	°C			
Operating junction temperature range	Tj	-40~125	°C			
Repetitive peak off-state voltage (T =25°C)	V _{DRM}	1200/1600	V			
Repetitive peak reverse voltage (T =25°C)	V_{RRM}	1200/1600	V			
Non repetitive surge peak Off-state voltage	V _{DSM}	V_{DRM} +100	V			
Non repetitive peak reverse voltage	V_{RSM}	V_{RRM} +100	V			
RMS on-state current (T =100°C)	I _{T(RMS)}	75	A			
Non repetitive surge peak on-state current	I _{TSM}	700	A			
I ² t value for fusing (tp=10ms)	I²t	2450	A ² S			
Critical rate of rise of on-state curren $t(I = 2 \times IGT, tr \le 100 \text{ ns})$	di/dt	150	A/μS			
Peak gate current	I_{GM}	5	A			
Average gate power dissipation	P _{G(AV)}	2	W			

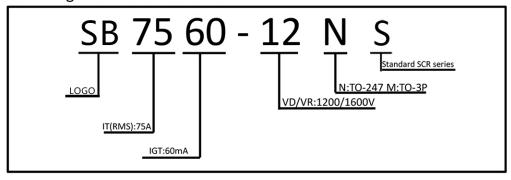
Thermal Resistances						
Symbol	Parameter	Value	Unit			
Rth(j-c)	Junction to case (DC)	TO-3P	0.60	°C/W		
		TO-247	0. 55			



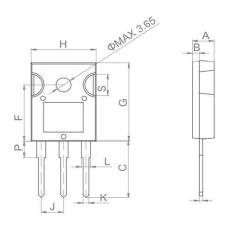
ELECTRICAL CHARACTERISTICS (T=25°Cunless otherwise specified)						
Symbol	Test Condition	Value			Unit	
		MIN.	TYP.	MAX.	Unit	
I_{GT}	$V = 12V R = 140\Omega$		40	60	mA	
V_{GT}				1. 3	V	
V_{GD}	VD=VDRM Tj=125°C R=1KΩ	0.2			V	
I_{L}	$I_G=1.2I_{GT}$			300	mA	
I_{H}	IT=50mA			200	mA	
dV/dt	$V_D=2/3V_{DRM}$ Gate Open Tj=125°C	500			V/µs	

STATIC CHARACTERISTICS							
Symbol	Parameter	Value(MAX.)	Unit				
V_{TM}	ITM =140A tp=380μs	Tj =25°C	1.8	V			
I_{DRM}	V -V V -V	Tj =25°C	200	μΑ			
I_{RRM}	$V_D = V_{DRM} V_R = V_{RRM}$	Tj =125°C	8	mA			

Ordering Information Scheme



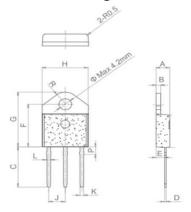
TO-247 Package Mechanical Data



	Dimensions						
Ref.	Millimeters			Inches			
	Min.	Тур-	Max.	Min.	Typ.	Max.	
A	4.9		5.4	0.193		0.213	
В	1.6		2.0	0.063		0.079	
С	14.35		15.4	0.565		0.606	
D	0.5		0.8	0.020		0.031	
F	14.4		15.1	0.567		0.594	
G	19.7		20.6	0.775		0.811	
Н	15.4		16.2	0.606		0.638	
J	5.3		5.6	0.209		0.220	
K	1.3		1.5	0.051		0.059	
L	2.8		3.3	0.110		0.130	
P	3.7		4.2	0.146		0.165	
S	5.35		5.65	0.211		0.222	



TO-3P Package Mechanical Data



	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур-	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
В	1.40		1.60	0.055		0.062
С	15.48		15.88	0.609		0.625
D	0.50		0.70	0.019		0.027
Е	2.70		2.90	0.106		0.114
F	15.92		16.32	0.626		0.642
G	20.27		20.67	0.798		0.813
Н	15.15		15.35	0.590		0.604
J		5.45			0.214	0.216
K	1.10		1.30	0.043		0.051
L	1.15		1.35	0.045		0.053
P	2.68		3.08	0.105		0.121
R		4.20			0.165	



FIG.1 Maximum power dissipation versus on-state current

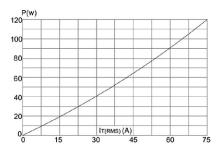


FIG.3: Surge peak on-state current versus number of cycles

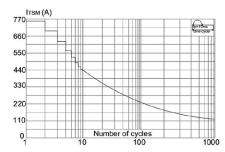


FIG.5: Non-repetitive surge peak on-state currentfor a sinusoidal pulse with width tp<10ms, and corresponding value of I2 t (dI/dt $< 50A/\mu s$)

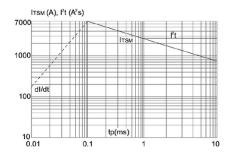


FIG.2: on-state current versus case temperature

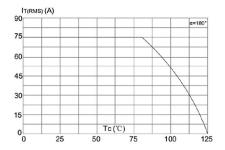


FIG.4: On-state characteristics (maximum values)

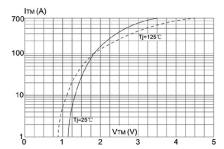


FIG.6: Relative variations of gate trigger current holding current and latching current versus junction temperature

